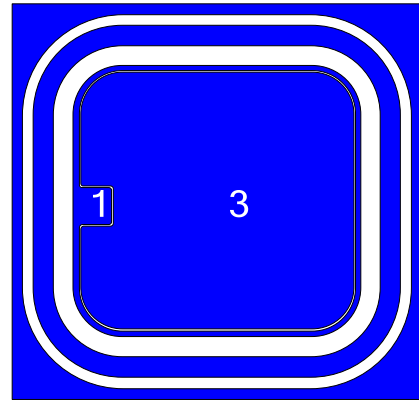


3VD156600YL HIGH VOLTAGE MOSFET CHIPS

DESCRIPTION

- 3VD156600YL is a High voltage N-Channel enhancement mode power MOS-FET chip fabricated in advanced silicon epitaxial planar technology.
- Advanced termination scheme to provide enhanced voltage-blocking capability.
- Avalanche Energy Specified.
- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- The chips may packaged in TO-92DT-3L type and the typical equivalent product is 1N60SS.
- The packaged product is widely used in AC-DC power suppliers, DC-DC converters and H-bridge PWM motor drivers.
- Die size: 1.6mm*1.54mm.
- Chip Thickness: 300±20μm.
- Top metal: Al, Backside Metal : Ag.



1-Gate PAD 3-Source PAD

CHIP TOPOGRAPHY

ABSOLUTE MAXIMUM RATINGS (T_{amb}=25°C)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V _{DS}	600	V
Gate-Source Voltage	V _{GS}	±30	V
Drain Current	I _D	500	mA
Operation Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C)

Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	V(BR)DSS	V _{GS} = 0V, I _D =250μA	600	---	---	V
Gate-Threshold Voltage	V _{th(GS)}	I _D =250μA, V _{DS} =V _{GS}	2.0	---	4.0	V
Gate-Body Leakage	I _{GSS}	V _{GS} =±30V, V _{DS} =0V	---	---	±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =600V, V _{GS} =0V	---	---	1.0	μA
Drain-Source On-Resistance	R _{DS(on)}	I _D =0.5A, V _{GS} =10V	---	---	13.5	Ω
Source-Drain Diode Forward On Voltage	V _{FSD}	I _D =0.8A, V _{GS} =0V	---	---	1.0	V